Elektronische Bauelemente

BD034

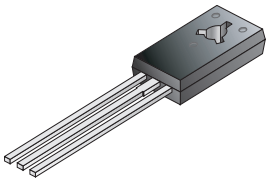
PNP General Purpose Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead free

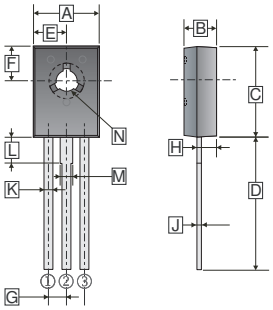
FEATURES

- High Current
- High Transition Frequency

TO-126



①Emitter
②Collector
③Base



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	7.40	7.80	H	1.10	1.50
B	2.50	2.90	J	0.45	0.60
C	10.60	11.00	K	0.66	0.86
D	15.30	15.70	L	2.10	2.30
E	3.70	3.90	M	1.17	1.37
F	3.90	4.10	N	3.00	3.20
G	2.29 TYP.				

CLASSIFICATION OF h_{FE}

Product-Rank	BD034-R	BD034-S	BD034-T
Range	100~200	140~280	200~400

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector - Base Voltage	V_{CBO}	-110	V
Collector - Emitter Voltage	V_{CEO}	-95	V
Emitter - Base Voltage	V_{EBO}	-7	V
Collector Current -Continuous	I_C	-2.5	A
Collector Power Dissipation	P_C	1.25	W
Maximum Junction to Ambient	$R_{\theta JA}$	100	℃ / W
Junction, Storage Temperature	T_J, T_{STG}	150, -55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	-110	-	-	V	I_C= -0.1mA, I_E=0
Collector-emitter sustaining voltage [1]	$V_{CEO(SUS)}$	-95	-	-	V	I_C= -10mA, I_B=0
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	-7	-	-	V	I_C=0, I_E= -0.1mA
Collector Cut - Off Current	I_{CBO}	-	-	-1	μA	V_{CB}= -100V, I_E= 0
Emitter Cut-Off Current	I_{EBO}	-	-	-1	μA	V_{EB}= -5V, I_C= 0
DC Current Gain [1]	h_{FE}	100	-	400		V_{CE}= -2V, I_C= -100mA
		40	-	-		V_{CE}= -2V, I_C= -1.5mA
Collector - Emitter Saturation Voltage [1]	$V_{CE(sat)}$	-	-	-0.5	V	I_C= -2A, I_B = -200mA
Base – Emitter Voltage [1]	V_{BE}	-	-	-1	V	V_{CE}= -5V, I_C= -500mA
Transition frequency	f_T	3	-	-	MHz	V_{CE}= -1V, I_C= -250mA, f=1MHz